Crystal growth and the piezoelectric property of the Ca₃NbGa₃Si₂O₁₄ compound

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A new piezoelectric Ca₃NbGa₃Si₂O₁₄ (CNGS) single crystal was synthesized by a solid state reaction and grown and Czochralski technique. The crystal structure of the CNGS was found to be isostructural with La₃Ga₅SiO₁₄ (LGS). The parameters were a=0.087 nm and c=0.4989 nm and the space group was P321. The distribution of each cation be ordered in each site. Some piezoelectric properties of CNGS are given.

Key words: Ca₃NbGa₃Si₂O₁₄, Czochralski, Structure, Piezoelectric.

Introduction

New compositions isostructural with La₃Ga₅SiO₁₄ (LGS) have been studied, and some single crystals of the new compositions showed piezoelectric properties higher than LGS. Such promising findings have led to continuous research in crystal growth of these and other new compositions, and efforts to find improved characteristics continue [1-4].

The LGS crystal belongs to the trigonal system, and has four kinds of cation sites in the structure represented as A₃BC₃D₂O₁₄ [5-11]. In this chemical formula, A and B represent a decahedral site coordinated by eight oxygen atoms, and an octahedral site coordinated by six oxygen atoms, respectively. While both C and D represent tetrahedral sites coordinated by four oxygen atoms; the size of the D site is slightly smaller than that of the C site.

In this research, a Ca₃NbGa₃Si₂O₁₄ (CNGS) composition was synthesized through a solid state reaction by partially substituting with Ca²⁺ and Nb⁵⁺ in the A and B sites in A₃BC₃D₂O₁₄-type structure. The melting point of the synthesized powder was investigated using differential thermal analysis and grown into a single crystal by the Czochralski method. The linear thermal expansion of the grown crystal was measured along all three axes using a dilatometer. The crystal structure was analyzed by refining the diffraction data of the single crystal using the WinRietveld program. The CNGS crystal's lattice constant gave almost constant values of a=0.085±0.0002 nm along the growth axis.

For application in piezoelectric devices, the quality factor, the electromechanical coupling factor and the

piezoelectric modulus of the CNGS crystal were measured.

Experimental Procedure

High purity powders (CaCO₃, Nb₂O₅, GaO₅ of 4N and above were homogeneously heated at 1150°C for 12 hours. The synthesize were analyzed by powder XRD in the region to 60° of its 2θ value. A scan speed degrees/minute and taken at 0.014 degree Differential thermal analysis (TGD 9700. RIKO) was carried out to investigate the means of the CNGS composition. The CNGS composition was heated to 1300°C at a heating rate of 100.

A single crystal of the CNGS composition by the Czochralski (CZ) method. The functional RF heated CZ furnace with a crucible (50 mm × 50 mm). The grown consisted of a mixture of Ar and 2 volds order to decrease the evaporation of galliant the melt during growth. The pulling and crystal rates were 1.0 mm/h and 10 rpm, respectively a speciment along the x, y and z axis over a temperature 25°C to 1000°C using a differential dilatomer. Mac science co.), comparing the length between a standard and the test sample rate was 10 K/minute and Al₂O₃ was standard specimen.

The structure analysis of the CNGS carried out using a single crystal X-ray data were collected at a scanning step, from 10° to 110°, at 0.02° intervals.

The WinReitveld program was used for the ment of the structural parameters. Lattice the CNGS crystal were calculated using the lattice of the control of the

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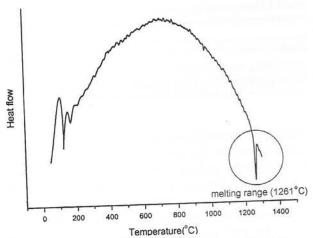


Fig. 1. Differential thermal analysis measured until 1300°C.

method along the growth axis.

To investigate the piezoelectric properties of the CNGS crystal, X-cut resonators of 10 mm × 3 mm × 0.5 mm in dimension were cut and polished. The quality factor, the electromechanical coupling factor and the piezoelectric modulus were evaluated by measuring the dielectric constant and the resonance and anti-resonance frequencies of these resonators in the thickness-longitudinal mode.

Result and Discussion

XRD analysis of the CNGS composition synthesized through a solid state reaction showed the phases present to be isostructural to LGS. DTA results to investigate the melting point are shown in Fig. 1. A marked endothermic reaction occurred at 1261°C, and this temperature was considered to be the melting point of CNGS.

The single crystal was grown by the CZ method. The diameter and length of the CNGS crystal were 21 mm and 120 mm, respectively. It was also partially transparent and used approximately 30% of the initial charge. Figure 2 shows the (001) plane cut vertical to the growth direction.

The linear thermal expansion properties of the 2 specimens measured along the x and y axis showed them to increase at a fixed rate, while the linear thermal expansion property of the specimen measured along the z axis showed it to exhibit a smaller thermal expansion rate than the x, y axes above 600°C. These results are illustrated in Fig. 3, and thermal expansion coefficient $(\alpha_{11} = 7.50 \times 10^{-6}/\text{K}, \ \alpha_{22} = 7.73 \times 10^{-6}/\text{K}, \ \alpha_{33} = 6.09 \times 10^{-6}/\text{K})$ of specimens along x, y and z axis were obtained.

The crystal structure of CNGS was found to be isostructural with $A_3BC_3D_2O_{14}$. The unit cell parameters were a=0.80873 nm and c=0.49798 nm and the space group was P321. The final R and $R_{\rm w}$ values for the refinement with anisotropic temperature factors were



Fig. 2. CNGS crystal cut vertical along growth axis.

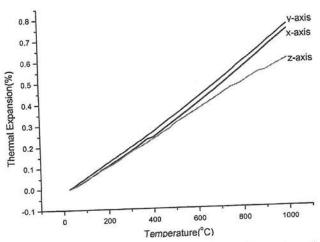


Fig. 3. The linear thermal expansion along x, y and c axis until 1000°C.

0.073 and 0.075, respectively. The converged structural parameters and the selected interatomic distances are given in Table 1 and Table 2, respectively.

The decahedral (3e) site was occupied by Ca, while the octahedral (1a) site was mostly occupied by Nb and partially by Ga, whereas La occupies the decahedral and Ga occupies the octahedral site in the LGS. The occupancies of these atoms were determined to be as follows; Ca=1 at 3e site, Nb:Ga=0.94:0.06 at 1a one, Si=1 at 2d one, Ga=1 at 3f one. These results clearly

Table 1. Atomic parameters of CNGS with estimated standard deviations in parentheses

Atom	Site	x	у	Z	В
	3e	0.4299(8)	0	0	1.5730(8)
Ca		0.4255(0)	0	0	0.7473(8)
Nb	1a	0	0	0	0.7473(8)
Ga	0.1	1/3	2/3	0.4450(9)	0.6130(9)
Si	2d	700	0	1/2	1.1876(7)
Ga	3f	0.7440(3)	2/3	0.4450(9)	2.7813(3)
01	2d	1/3		0.6954(1)	1.8896(2)
O2	6g	0.4944(1)	0.3220(9)	0.0954(1)	0.3317(4)
O3	6g	0.2387(1)	0.0749(4)	0.2230(1)	0.0017(1)

Table 2. Selected interatomic Distances for CNGS

La polyhedron	Nb octahedron	
Ca - O1 × 2 2.614(5)	Nb - O3 × 6 2.044(5)	
$O2 \times 22.338(6)$		
$O2' \times 2 \ 2.828(5)$		
$O3 \times 2 \ 2.225(5)$		
(Ca-O)av 2.501		

Si tetrahedron	Ga tetrahedron	
Si - O1 × 1 1.731(6)	Ga - O2 × 2 1.979(9)	
$O2 \times 3 \ 1.520(6)$	$O3 \times 2 \ 1.958(1)$	
(Si-O)av 1.626	(Ga-O)av 1.969	

indicated that each site was fully occupied by each metal. The distribution of all metals finally determined was $(Ca_3)^{3e}(Nb)^{1a}(Ga_3)^{3f}(Si_2)^{2d}O_{14}$ with the Wyckoff-site notation superscripted. Since this distribution is uncommon among the LGS-type crystals which have been grown thus far, the piezoelectric properties of CNGS crystal were expected to be different from the other LGS-type crystals investigated.

Ca atoms are coordinated to eight O atoms, at distance 0.2225(5)-0.2828(5) nm, forming a distorted cubic antiprism. The average B-O distance (0.2044 nm) is longer than the estimated Nb-O distance (0.2002 nm) and the corresponding one in LNG (2.007 Å). [12-13] The mean Ga-O distance (0.1969 nm) is apparently longer than the mean Si-O distance (0.1626 nm), and the shape of the Ga tetrahedron appears to be more distorted.

Figure 4 shows the lattice parameter variation of the crystal boule grown from the stoichiometric melt composition as a function of the solidified fraction $g = W_{crystal}/W_{initial}$, where $W_{crystal}$ and $W_{initial}$ are the weights of the grown crystal and starting melt, respectively. It was found that the lattice parameter remained almost constant with a value of a=0.8085 \pm 0.0002 nm from the

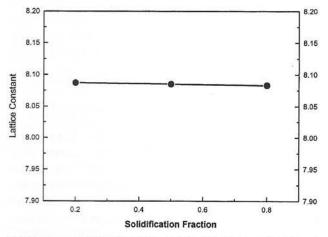


Fig. 4. Lattice constant along the growth direction as a function of solidified fraction, g.

Table 3. Piezoelectric properties of grown CNGS and

	LGS [5]	CNE
Quality factor	30000	5600
Piezoelectric strain constant (d ₁₁ , 10 ⁻¹² C/N)	-6.16	-33
Electromechanical coupling factor (K ₁₂ , %)	16	

shoulder to the tail part of the grown crystal suggests that the stoichiometric composition of the congruently melting congruently melting composition of the congruently melting composition of the congruently melting congruently melting

The measured results of CNGS crystal's properties are shown in Table 3. The quality electromechanical coupling factor (K_{II}) and electric modulus (d₁₁) of the CNGS crystal than those of LGS. It was assumed that the factor will have a lower elastic loss and a mechanical coupling factor, while the modulus will result in an improved prevention perty compared with LGS.

Conclusions

A CNGS compound synthesized by a reaction was grown into a uniform single cross the [001] direction using the CZ method analysis of the CNGS crystal was carried unsingle crystal XRD. In this structural assumed that the CNGS crystal obtained partial substitution of Ca, Nb formed a stable assumed structure.

The lattice parameters measured along dedirection indicated that the CNGS crystal establishmetric composition from the shoulder

The quality factor, the electromechanical factor (K₁₂) and the piezoelectric modules of CNGS crystal were found to be higher than LGS.

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